



Developments for low background experiments

DASTGHEIBI FARD Ali 24-26 June 2024 GDR DI2I



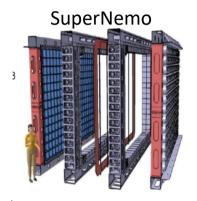


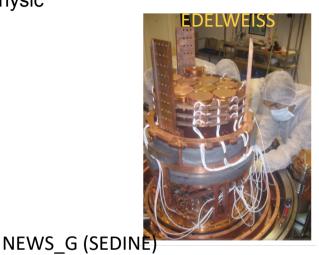
What means Low background experiments

- Looking for rare events:
 - Fondamental Physics
 - Proton decay
 - Nuclear structure
 - Neutrinon double beta decay ßßv0
 - Dark matter
 - Other disciplines
 - Low radioactivity measurement
 - Logical test failure in nano/micro electronics
 - Qubits (Quantum computing)
 - Biology
- Protected from any irradiation
 - Cosmic rays
 - Natural irradiation
 - Radon
- Located in the Underground Laboratory (UL)
- Experiment components are radiopure

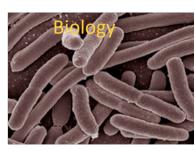
Example of the experiments

Fondamental Physic





Other disciplines

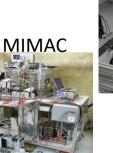




Gamma spectrometry











Then TESSERACT; Qubits

Common part of LB experiments

- Material selection
- Low radioactive components such as:
 - Electronics components
 - Shielding
 - ==> Standard Lead
 - ==> Ancient Lead
 - Detector structures/support
 - ==> Copper mainly
 - Commercial production ≈ 5N (99.999%) ≈ 0.1-10 mBq/kg
 - **Electroform Copper** ≈ 6N (99,9999%) ≈ 10-100 nBq/kg

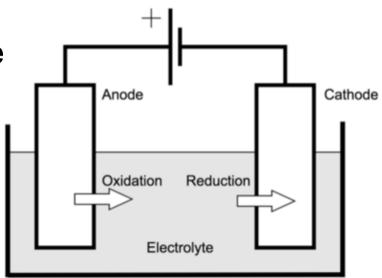
Electrolytic Cell and Electroplating

- Electrolytic cell driven by oxidation and reduction reactions
- Current supplied to drive reactions
- Desired result is generally the reduction of ions from the electrolyte to form atoms on the cathode surface
- Mass deposited proportional to current supplied:

$$M = \frac{m_r \int I(t) dt}{zF}$$

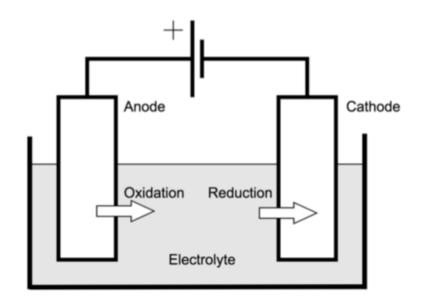
m_- molar mass I(t) – current as function of time z- number of electrons transferred in reduction reaction F - Faraday Constant (= $e N_{\star}$)

M - mass



Electroplating Copper

- Some ions reduce more readily than others –
 reduction potentials
- Voltage between anode and cathode limits electroplating of some species
- Copper benefits from 'electrowinning' high reduction potential +0.34 V
- Reduction potential of:
 - Uranium: -1.80 V
 - Thorium: -1.90 V
 - Lead: -0.44 V
- All lower than copper; refined during electroplating



Why don't impurities plate too?

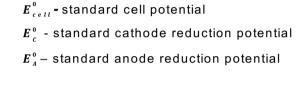
 Which reaction proceeds determined by standard cell potential:

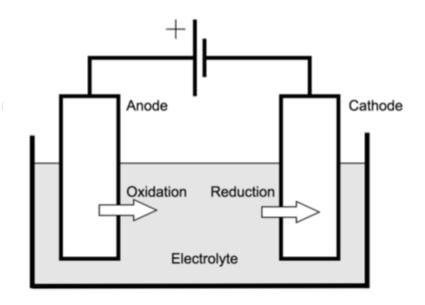
$$E_{cell}^0 = E_C^0 - E_A^0$$

Related to Gibbs Free Energy:

$$\Delta G^0 = -z \, F \, E_{cell}^0$$

- If $\Delta G^0 < 0$ reaction is spontaneous
- If $\Delta G^0 > 0$ need extra energy input





An Example

 E_{cell}^{0} - standard cell potential

Anode

Oxidation

Reduction

Electrolyte

Cathode

 E_c^0 - standard cathode reduction potential

 E_A^0 – standard anode reduction potential

- Example of solution containing U³⁺ and Cu²⁺, with a Cu anode:
 - U³⁺ to U

- E_Cell= -2.138 V → Requires energy Cu²⁺ to C

- Cu²⁺ to Cu
 - E_Cell= 0 V → In equilibrium
- Cu²⁺ reduction will occur at lower potential
- Still require a potential difference between electrodes to overcome energy losses

Detector Hemispheres

- Two 140 cm diameter hemispheres
- 4N copper (99.99% pure)
- Plates purchased and then spun into hemispheres
- 110 cm diameter hemisphere also spun as the anode for electroplating





Preparation Procedure

- Cleaned with domestic detergent
- Sanded different sanding for each hemisphere – but final stage with silicon carbide paper
- Estimated ~10-100 μm removed by sanding (~500 μm second hemisphere)
- Cleaned with **Micro90** detergent (1%) in deionised water
- Inner hemisphere received same treatment for first use – just Micro90 second time



Chemical Etching

- Surface chemically etched with 3
 % H202, 1 % H2SO4 in deionised
 (DI) water
 - Shown to be effective etchant while less aggressive than some alternatives
- -To remove any trapped particulates from spinning process or sanding, and make surface more smooth
- Estimate **5-10 μm** removed during etching





Cleanroom





Process carried out in cleanroom to minimise contamination and particulates

Electrolyte

- First hemisphere filled with 80 I electrolyte from SEDINE electroplating,
 5.5 I H2SO4 and topped up to ~300 I with DI water
- Second hemisphere used ~275 I first-hemisphere electrolyte, 2 I H2SO4 and up to ~300 I with DI water
- Both have some CuSO4 in solution already
- Pump and filter used to move electrolyte and remove particulates

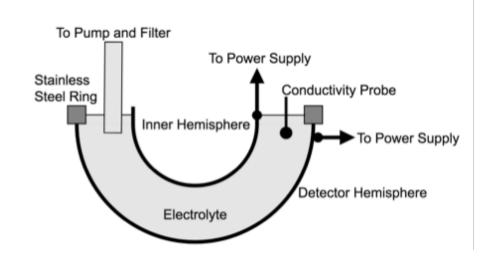


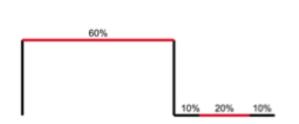
Electropolishing

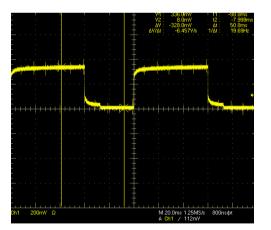
- Electropolishing serves several purposes
 - Removes layer from hemisphere without chemical or mechanical attack
 - Preferentially removes high spots from surface
 - Increases concentration of CuSO4 in electrolyte
- Waveform used to polish
 - +ve = detector hemisphere

voltage>inner hemisphere

- First (second) hemisphere 21.2±0.1 μm (28.2±0.1 μm) polished

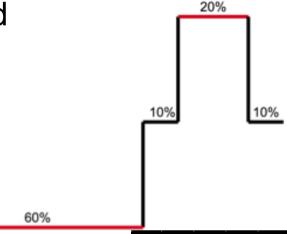


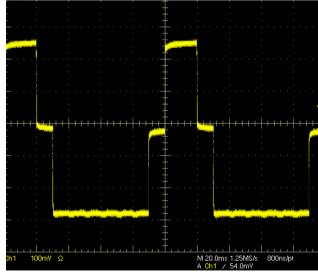




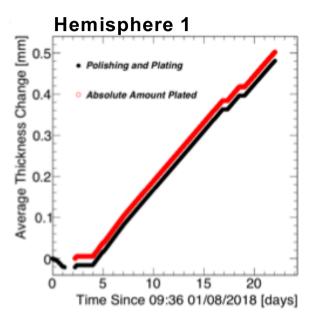
Why Pulse-Reverse Plating?

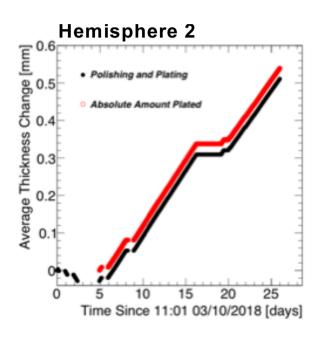
- Waveform for plating with relaxation period and/or reverse bias (effectively polishing)
- Benefits compared to DC plating:
 - High points are preferentially removed in reverse bias section
 - Greater uniformity of plate relaxation period allows diffusion of ions
 - Higher density copper plate





Electroplating





- Plated for approximately 20 days for both hemispheres
- 0.27 to 0.3 V amplitude in forward and reverse directions of plating
 - Established value for copper plating
- In total first (second) hemisphere plated 502.1 \pm 0.2 μ m (539.5 \pm 0.2 μ m)

Results

- Drained electrolyte and rinsed surface with DI water
- Passivated with 1% C6H8O7 in DI water for 30 min-1 hour
- Prevents further oxidisation
- Rinsed again with DI water
- Stored in plastic ready for electron beam welding



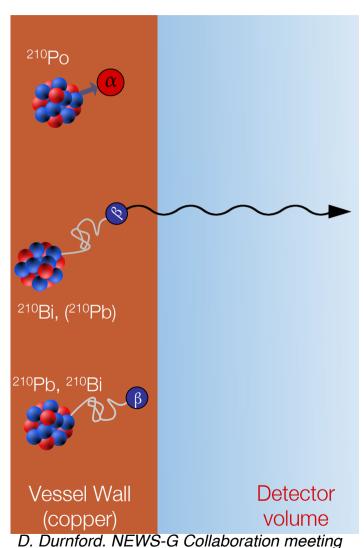


- First hemisphere had many nodules frequent and 0.5-1.5 mm in height
- Second hemisphere had very few nodules

Hemispheres 1st / 2nd

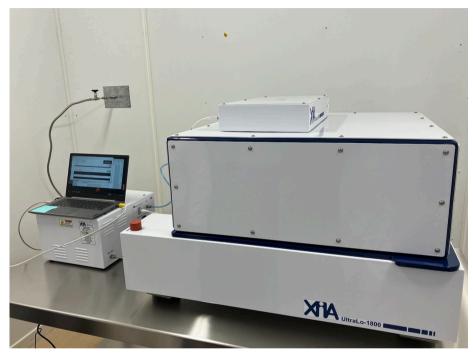
- Second hemisphere has less nodules. Main difference with first hemisphere:
 - Higher initial CuSO₄ concentration already used for one hemisphere
 - But also:
 - More sanding ensure uniform surface before beginning
 - Pump outlet moved daily improve mixing and spread excess-plating
 - Improved electrical isolation from container
 - Maybe higher H2SO4 concentration (to be determined by analysis)
 - Solution filtered for longer before beginning and between polishing and plating
 - Inner hemisphere had layer removed from polishing already

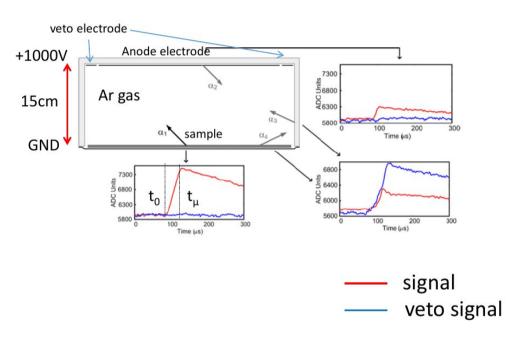
Then, surface contamination



- 210Pb is a long-lived radioimpurity found in copper
- Most radiation is stopped inside the copper but...
 - Bremsstrahlung x-rays (~keV) from 210Pb and 210Bi β- decay in the copper escape, travel through whole volume

XIA, Ultralo-1800 Alpha counter

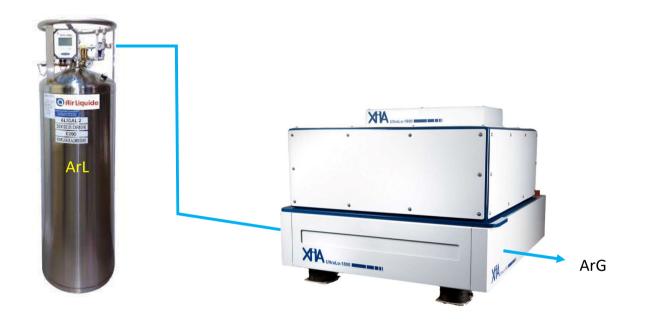




- Installation in a Cleanroom @ LPSC for commissioning run
- Final installation @ LSM

 By measuring rise time (t_μ - t_0), surface event can be distinguished from event in Ar gas or celling

How XIA operate



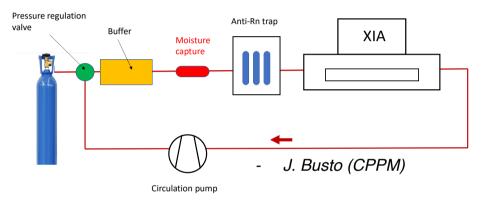
Flushing : ~ 700 L (45 min)

Mesurement: ~300 L/h

Proposition: replace Liquid-Ar by Gas-Ar and operate in a closed circuit with an anti-Rn purification system and very low moisture.

Using XIA in a closed circuit

Basic desing



- Development of GPS: Gas Purification System
- Manufacture is finished
- Pre-Installation @LPSC
- To be operational after confirming the XIA "normal" operating mode



Conclusion

- Radiopurity of off-the-shelf copper not sufficient Solution: electroplate 0.5 mm ultra-pure copper layer to remove alpha particle component
- Electrode potential can be selected to plate only copper but not U, Th and Pb
- Surface preparation is critical sanding, cleaning and etching
- Electropolished ~20 μm from surface and electroplated ~500 μm ultra-pure copper
- Difference in surface quality between the two hemisphere
- Measurement of the surface is necessary by an Alpha Counter
- For the cost and environment reason, gas purification and circulation system is welcome =>if the XIA operation mode is respected

